



VOID-LESS HERMETICALLY SEALED ULTRAFAST RECOVERY GLASS RECTIFIERS
 Qualified per MIL-PRF-19500/477

Qualified Levels:
 JAN, JANTX,
 JANTXV and JANS

DESCRIPTION

This “Ultrafast Recovery” rectifier diode series is military qualified and is ideal for high-reliability applications where a failure cannot be tolerated. The industry-recognized 6.0 amp rated rectifiers with working peak reverse voltages from 50 to 150 volts are hermetically sealed with void-less glass construction using an internal “Category 1” metallurgical bond. These devices are available in both leaded and surface mount MELF package configurations. Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time requirements including standard, fast and ultrafast device types in both through-hole and surface mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 1N5807, 1N5809, 1N5811 series.
- Void-less hermetically sealed glass package.
- Quadruple-layer passivation.
- Extremely robust construction.
- Internal “Category 1” metallurgical bonds.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/477.
- RoHS compliant versions available (commercial grade only).

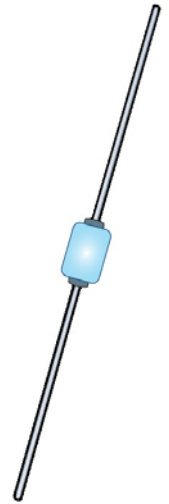
APPLICATIONS / BENEFITS

- Ultrafast recovery 6 amp rectifier series from 50 to 150 V.
- Military, space and other high-reliability applications.
- Switching power supplies or other applications requiring extremely fast switching & low forward loss.
- High forward surge current capability.
- Low thermal resistance.
- Controlled avalanche with peak reverse power capability.
- Inherently radiation hard as described in Microsemi [MicroNote 050](#).

MAXIMUM RATINGS @ T_A = 25 °C unless otherwise specified

| Parameters/Test Conditions | Symbol | Value | Unit |
|---|-------------------------------------|------------------|------|
| Junction and Storage Temperature | T _J and T _{STG} | -65 to +175 | °C |
| Thermal Resistance Junction-to-Lead (L = .375 in) Fig. 1 | R _{θJL} | 22 | °C/W |
| Thermal Resistance | R _{θJX} | 52 | °C/W |
| Working Peak Reverse Voltage: | V _{RWM} | 50 100 150 | V |
| Forward Surge Current ⁽³⁾ | I _{FSM} | 125 | A |
| Average Rectified Output Current @ T _L = +75 °C at 3/8 inch lead length ⁽¹⁾ | I _{O1} | 6.0 | A |
| Average Rectified Output-Current @ T _A = +55 °C at 3/8 inch lead length ⁽²⁾ | I _{O2} | 3.0 | A |
| Capacitance @ V _R = 10 V, f = 1 MHz; V _{sig} = 50 mV (p-p) | C _J | 60 | pF |
| Reverse Recovery Time ⁽⁴⁾ | t _{rr} | 30 | ns |
| Solder Temperature @ 10 s | T _{SP} | 260 | °C |


- Notes:**
1. I_{O1} is rated at T_L = 75 °C at 3/8 inch lead length. Derate at 60 mA/°C for T_L above 75 °C.
 2. I_{O2} is derated at 25 mA/°C above T_A = 55 °C for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where T_{J(max)} 175 °C is not exceeded.
 3. T_A = 25 °C @ I_O = 3.0 A and V_{RWM} for ten 8.3 ms surges at 1 minute intervals.
 4. I_F = 1.0 A, I_{RM} = 1.0 A, I_{R(REC)} = .0.10 A and di/dt = 100 A/μs min.



“B” Package

Also available in:

“B” MELF Package
 (surface mount)

 [1N5807, 09, 11US & URS](#)

MSC – Lawrence

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 Lawrence, MA 01841
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 (978) 620-2600
 Fax: (978) 689-0803

MSC – Ireland

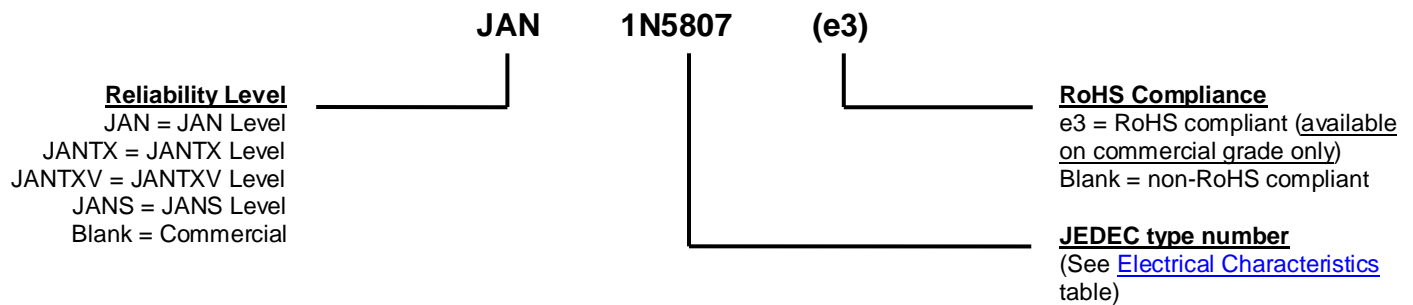
Gort Road Business Park,
 Ennis, Co. Clare, Ireland
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Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Tin/lead (Sn/Pb) or RoHS compliant matte/tin (commercial grade only) over nickel plate over copper.
- MARKING: Body coated in blue with part number.
- POLARITY: Cathode indicated by band.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 750 milligrams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

| Symbol | Definition |
|-----------|--|
| V_{BR} | Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current. |
| V_{RWM} | Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range. |
| I_O | Average Rectified Output Current: Output current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle. |
| V_F | Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current. |
| I_R | Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature. |
| C | Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage. |
| t_{rr} | Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current occurs. |

ELECTRICAL CHARACTERISTICS @ $T_A = 25^\circ\text{C}$ unless otherwise stated

| TYPE | BREAKDOWN VOLTAGE (MIN.) @ 100 μA $V_{(BR)}$ | MAXIMUM FORWARD VOLTAGE @ 4 A (8.3 ms pulse) V_{FM} | | REVERSE CURRENT (MAX.) @ V_{RWM} I_R | | SURGE CURRENT (MAX) I_{FSM} (Note 1) | REVERSE RECOVERY TIME (MAX) t_{rr} (Note 2) |
|--------|---|---|----------------------|--|----------------------|--|---|
| | | Volts | | μA | | | |
| | | 25 $^\circ\text{C}$ | 125 $^\circ\text{C}$ | 25 $^\circ\text{C}$ | 125 $^\circ\text{C}$ | | |
| 1N5807 | 60 | 0.875 | 0.800 | 5 | 525 | 125 | 30 |
| 1N5809 | 110 | 0.875 | 0.800 | 5 | 525 | 125 | 30 |
| 1N5811 | 160 | 0.875 | 0.800 | 5 | 525 | 125 | 30 |

- NOTES:** 1. $T_A = 25^\circ\text{C}$ @ $I_O = 3.0\text{ A}$ and V_{RWM} for ten 8.3 ms surges at 1 minute intervals.
 2. $I_F = 1.0\text{ A}$, $I_{RM} = 1.0\text{ A}$, $I_{R(REC)} = 0.10\text{ A}$ and $di/dt = 100\text{ A}/\mu\text{s min}$.

GRAPHS

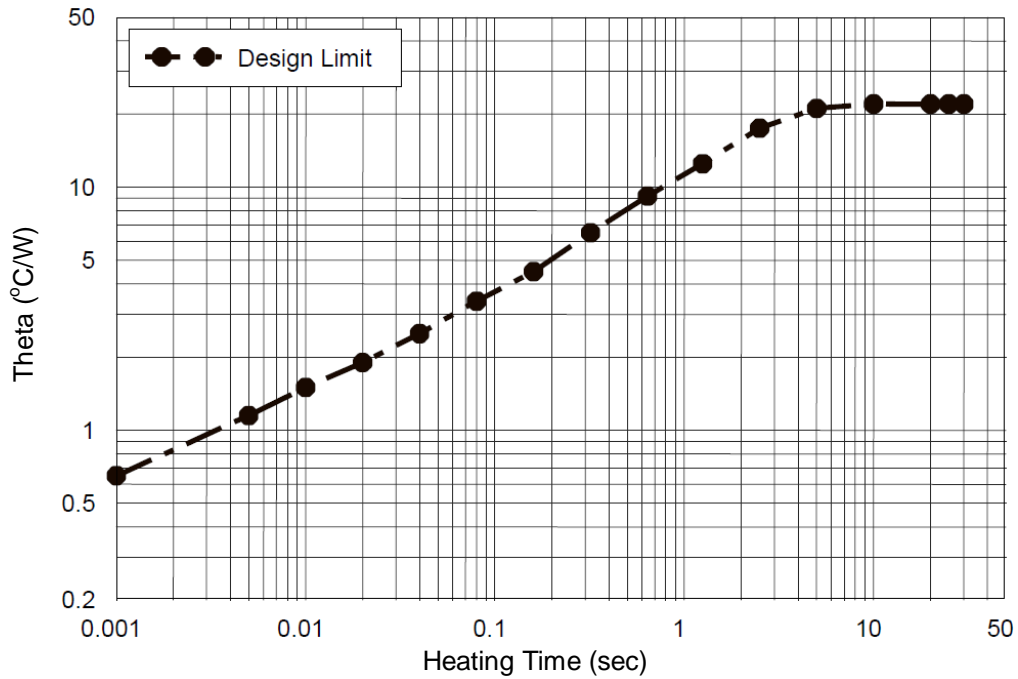


FIGURE 1
Maximum Thermal Impedance

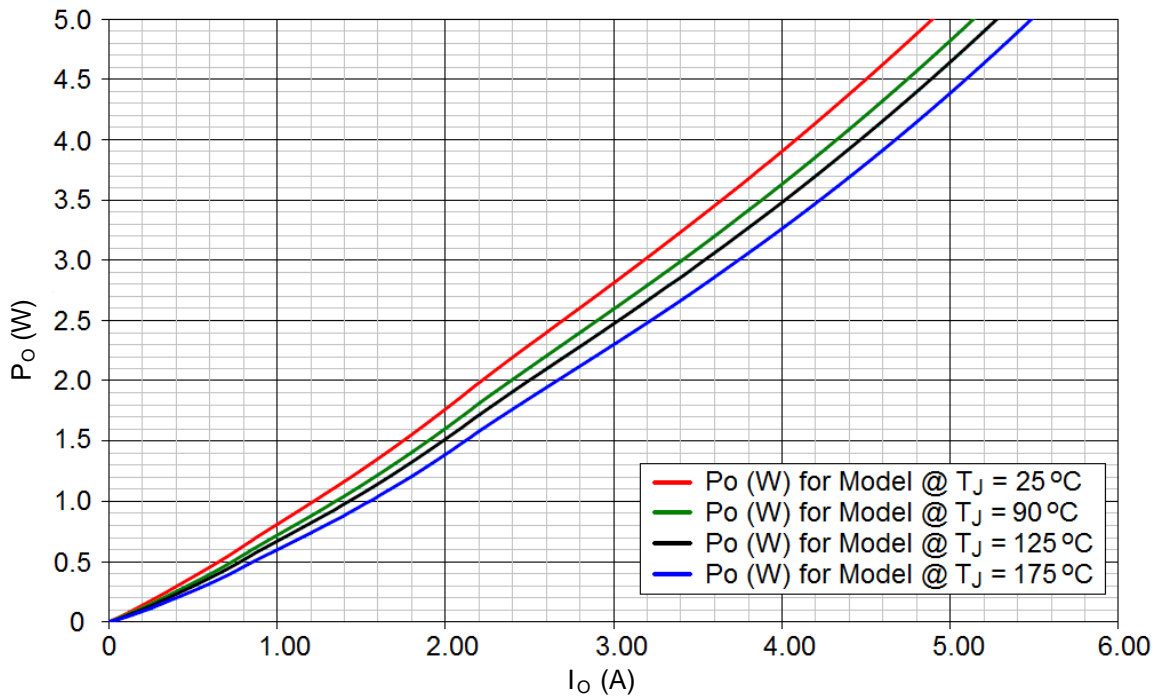


FIGURE 2
Rectifier Power vs I_O (Average Forward Current)

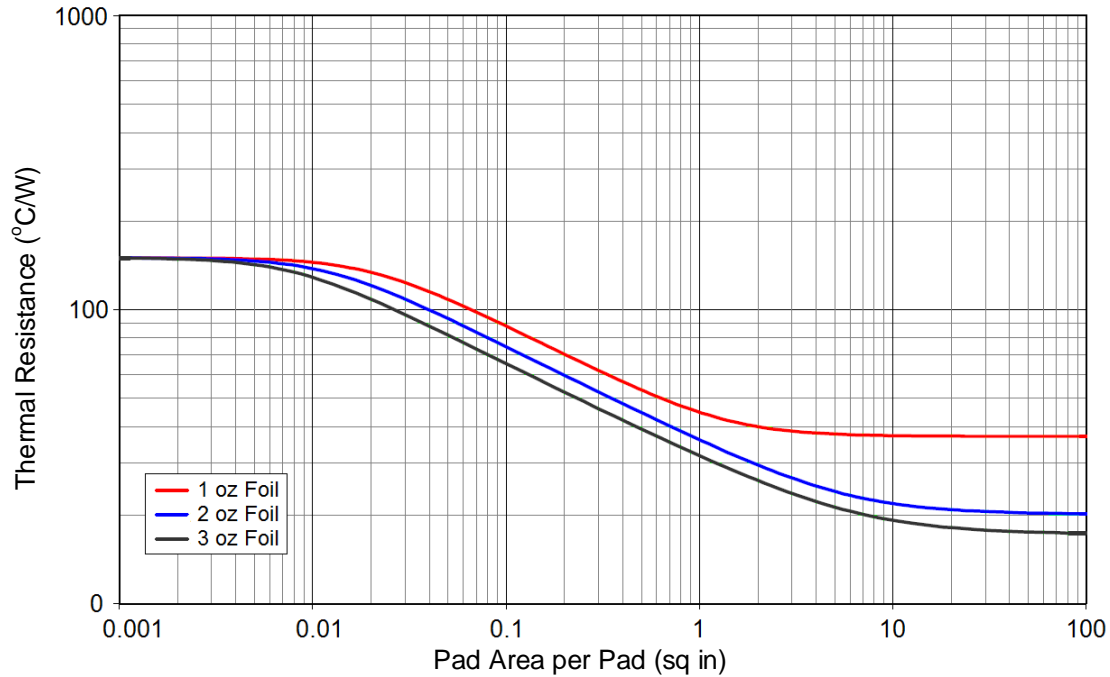
GRAPHS (continued)


FIGURE 3
Thermal Resistance vs FR4 Pad Area At Ambient
 PCB horizontal (for each pad) with 1, 2, and 3 oz copper

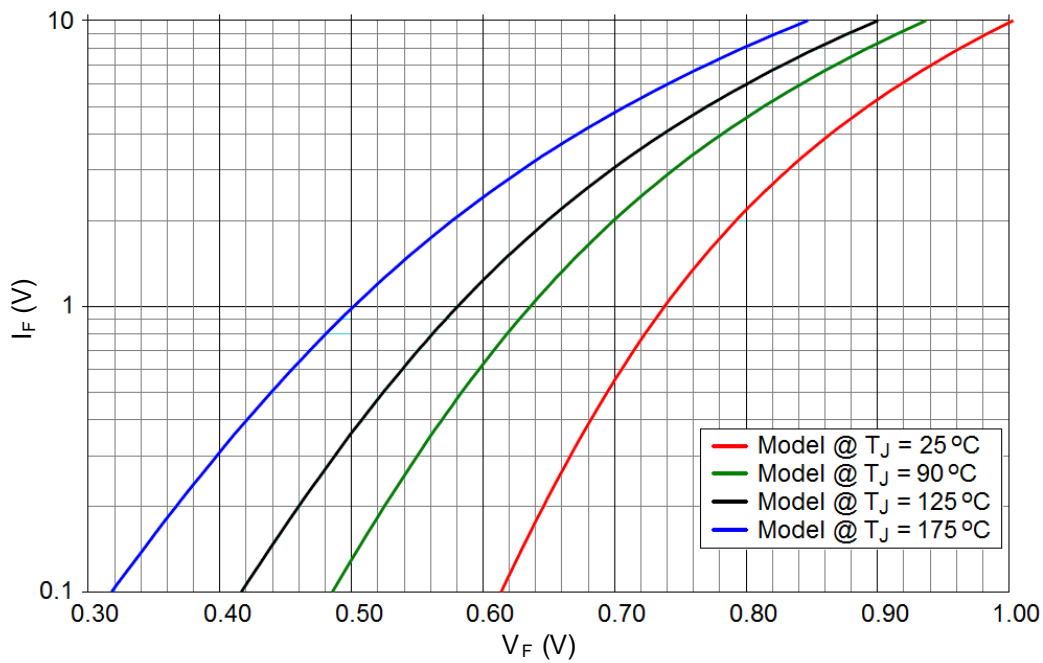
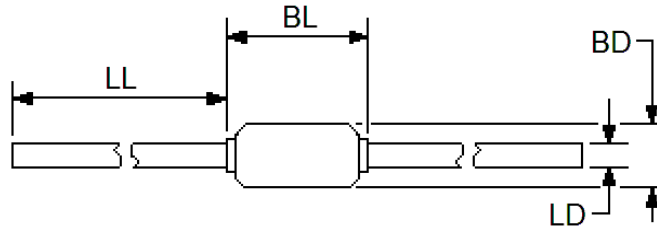


FIGURE 4
Forward Voltage vs Forward Current

PACKAGE DIMENSIONS

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension BL shall include the entire body including slugs and sections of the lead over which the diameter is uncontrolled. This uncontrolled area is defined as the zone between the edge of the diode body and extending .050 inch (1.27 mm) onto the leads.
4. Dimension BD shall be measured at the largest diameter.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

| Ltr | DIMENSIONS | | | | Notes |
|-----------|------------|------|-------------|-------|-------|
| | INCH | | MILLIMETERS | | |
| | Min | Max | Min | Max | |
| BD | .115 | .142 | 2.92 | 3.61 | 4 |
| BL | .130 | .300 | 3.30 | 7.62 | 3 |
| LD | 0.036 | .042 | 0.91 | 1.07 | 3 |
| LL | .900 | 1.30 | 22.86 | 33.02 | |
| | | | | | |

Lead Tolerance = +.002 - .003 in.

(Includes sections of the lead or fillet over which the lead diameter is uncontrolled.)

Mouser Electronics

Authorized Distributor

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Microchip:

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